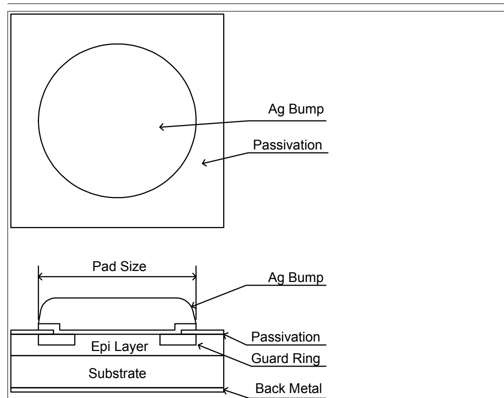
GOOD-ARK
SEMICONDUCTOR

GDSYQC15AP

Schottky Barrier Diode

70V Type For Glass Seal



Chip Information

Chip Size	0.35 x 0.35mm
Pad Size	0.14 x 0.14mm
Chip Quantity	90245 pcs/wafer
Scribe Line Width	50um
Passivation	PSG
Wafer Size	5 inch
Top Metallization	Ag Bump(For Glass Seal)

Chip Thickness/Back Metal : See below "Ordering Information"

MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	70	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR		V	
Average Forward Rectified Current	IF(AV)	200	mA	
Peak Forward Surge Current	IFSM	2	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Test Spec	Typical	Unit	Test Condition	
Maximum Forward Voltage	VF1	0.410	0.400	0.350	V	IF=1mA	Ta=25degC
	VF2	1.000	0.950	0.870	V	IF=15mA	Ta=25degC
	VF3				V		
	VF4				V		
	VF5				V		
Maximum DC Reverse Current	IR1	0.2	0.15	0.08	uA	VR=50V	Ta=25degC
	IR2				uA		
	IR3				uA		
	IR4				uA		
Reverse Breakdown Voltage	BV1	70	73	84	V	IR=10uA	
	BV2	70	73	84	V	IR=100uA	
	deltaBV	2.5	2		V	BV2-BV1	
Junction Capacitance	Cj			2.7	pF	V=0V,f=1MHz	
Reverse Recovery Time	trr				nS		

Ordering Information

Chip Type	Chip Thickness	Back Metal
GDSYQC15AP	150 +/- 20um	Ti-Ni-Ag(For Glass Seal)

Note:
Designed For 1N5711,1N6263

REV. 1